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With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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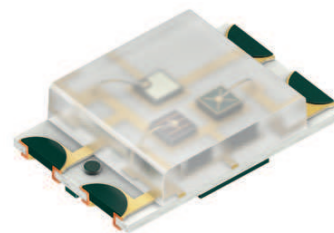
Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



Red (655 nm), Green (530 nm) and Infrared Emitter (940 nm)

Version 1.1

SFH 7013



Features:

- SMT package with red (655 nm), green (530 nm) and IR emitter (940 nm)
- Suitable for SMT assembly
- Available on tape and reel
- Emitters can be controlled separately
- Emitter 1 = red, Emitter 2 = green, Emitter 3 = IR

Applications

- Biomonitoring

Notes

Depending on the mode of operation, these devices emit highly concentrated non visible infrared light which can be hazardous to the human eye. Products which incorporate these devices have to follow the safety precautions given in IEC 60825-1 and IEC 62471.

Ordering Information

Type:	Package:	Ordering Code
SFH 7013	SMT Multi CHIPLED	Q65112A1316

Maximum Ratings

Parameter	Symbol	Values	Unit
Operating and storage temperature range	$T_{op}; T_{stg}$	-40 ... 85	°C
Reverse voltage	V_R	5	V
ESD withstand voltage (acc. to ANSI/ ESDA/ JEDEC JS-001 - HBM)	V_{ESD}	2	kV

Emitter 1

Forward current	I_F (DC)	40	mA
Surge current ($t_p \leq 100 \mu s$, $D = 0$)	I_{FSM}	0.6	A
Power consumption	P_{tot}	120	mW
Thermal resistance junction - ambient, mounted on PC-board (FR4) ^{1) page 19}	R_{thJA}	445	K / W

Emitter 2

Forward current	I_F (DC)	30	mA
Surge current ($t_p \leq 100 \mu s$, $D = 0$)	I_{FSM}	0.75	A
Power consumption	P_{tot}	90	mW
Thermal resistance junction - ambient, mounted on PC-board (FR4) ^{1) page 19}	R_{thJA}	565	K / W

Emitter 3

Forward current	I_F (DC)	60	mA
Surge current ($t_p \leq 200 \mu s$, $D = 0$)	I_{FSM}	1	A
Total power dissipation	P_{tot}	110	mW
Thermal resistance junction - ambient, mounted on PC-board (FR4) ^{1) page 19}	R_{thJA}	585	K / W

Note: The stated maximum ratings refer to one chip, unless otherwise specified.

Characteristics ($T_A = 25\text{ °C}$)

Parameter		Symbol	Values	Unit
Emitter 1				
Peak wavelength ($I_F = 20\text{ mA}$, $t_p = 20\text{ ms}$)	(typ)	λ_{peak}	660	nm
Centroid wavelength ($I_F = 20\text{ mA}$, $t_p = 20\text{ ms}$)	(typ)	$\lambda_{\text{centroid}}$	655	nm
Spectral bandwidth at 50% of I_{max} ($I_F = 20\text{ mA}$, $t_p = 20\text{ ms}$)	(typ)	$\Delta\lambda$	17	nm
Half angle	(typ)	φ	± 65	°
Dimensions of active chip area	(typ)	L x W	0.3 x 0.3	mm x mm
Rise and fall time of I_e (10% and 90% of $I_{e\text{ max}}$) ($I_F = 100\text{ mA}$, $R_L = 50\text{ }\Omega$)	(typ)	t_r, t_f	17	ns
Forward voltage ($I_F = 20\text{ mA}$, $t_p = 20\text{ ms}$)	(typ (max))	V_F	2.1 (≤ 2.8)	V
Reverse current ($V_R = 5\text{ V}$)		I_R	not designed for reverse operation	μA
Total radiant flux ($I_F = 20\text{ mA}$, $t_p = 20\text{ ms}$)	(typ)	Φ_e	12	mW
Radiant intensity ($I_F = 20\text{ mA}$, $t_p = 20\text{ ms}$)	(typ)	$I_{e, \text{typ}}$	4	mW/sr
Radiant intensity in axial direction ($I_F = 20\text{ mA}$, $t_p = 20\text{ ms}$)	(min)	$I_{e, \text{min}}$	2	mW / sr
Temperature coefficient of I_e or Φ_e ($I_F = 20\text{ mA}$, $t_p = 20\text{ ms}$)	(typ)	TC_I	-0.7	% / K
Temperature coefficient of V_F ($I_F = 20\text{ mA}$, $t_p = 20\text{ ms}$)	(typ)	TC_V	-1.7	mV / K
Temperature coefficient of wavelength ($I_F = 20\text{ mA}$, $t_p = 20\text{ ms}$)	(typ)	TC_λ	0.18	nm / K

Emitter 2

Peak emission wavelength ($I_F = 20\text{ mA}$, $t_p = 20\text{ ms}$)	(typ)	λ_{peak}	526	nm
Centroid wavelength ($I_F = 20\text{ mA}$, $t_p = 20\text{ ms}$)	(typ)	$\lambda_{\text{centroid}}$	530	nm
Spectral bandwidth at 50% of I_{max} ($I_F = 20\text{ mA}$, $t_p = 20\text{ ms}$)	(typ)	$\Delta\lambda$	32	nm
Half angle	(typ)	φ	± 65	°

Parameter		Symbol	Values	Unit
Dimensions of active chip area	(typ)	L x W	0.5 x 0.5	mm x mm
Rise and fall times of I_e (10% and 90% of $I_{e\max}$) ($I_F = 100\text{ mA}$, $R_L = 50\ \Omega$)	(typ)	t_r / t_f	59	ns
Forward voltage ($I_F = 20\text{ mA}$, $t_p = 20\text{ ms}$)	(typ (max))	V_F	3 (≤ 3.4)	V
Reverse current ($V_R = 5\text{ V}$)	(typ (max))	I_R	not designed for reverse operation	μA
Total radiant flux ($I_F = 20\text{ mA}$, $t_p = 20\text{ ms}$)	(typ)	Φ_e	11	mW
Radiant intensity ($I_F = 20\text{ mA}$, $t_p = 20\text{ ms}$)	(typ)	$I_{e, \text{typ}}$	3	mW/sr
Radiant intensity ($I_F = 20\text{ mA}$, $t_p = 20\text{ ms}$)	(min)	$I_{e, \text{min}}$	1	mW/sr
Temperature coefficient of I_e or Φ_e ($I_F = 20\text{ mA}$, $t_p = 20\text{ ms}$)	(typ)	TC_I	-0.35	% / K
Temperature coefficient of V_F ($I_F = 20\text{ mA}$, $t_p = 20\text{ ms}$)	(typ)	TC_V	-3.6	mV / K
Temperature coefficient of wavelength ($I_F = 20\text{ mA}$, $t_p = 20\text{ ms}$)	(typ)	TC_λ	0.03	nm / K

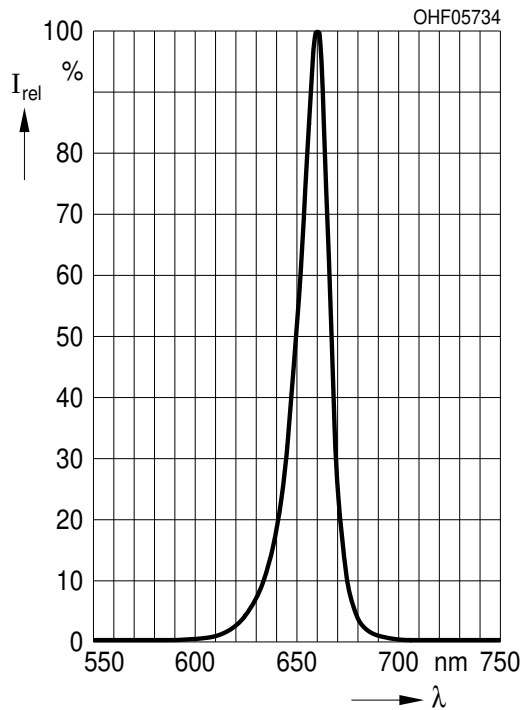
Emitter 3

Peak emission wavelength ($I_F = 20\text{ mA}$, $t_p = 20\text{ ms}$)	(typ)	λ_{peak}	950	nm
Centroid wavelength ($I_F = 20\text{ mA}$, $t_p = 20\text{ ms}$)	(typ)	$\lambda_{\text{centroid}}$	940	nm
Spectral bandwidth at 50% of $I_{\max}$ ($I_F = 20\text{ mA}$, $t_p = 20\text{ ms}$)	(typ)	$\Delta\lambda$	42	nm
Half angle	(typ)	φ	± 65	°
Dimensions of active chip area	(typ)	L x W	0.3 x 0.3	mm x mm
Rise and fall times of I_e (10% and 90% of $I_{e\max}$) ($I_F = 100\text{ mA}$, $R_L = 50\ \Omega$)	(typ)	t_r / t_f	16	ns
Forward voltage ($I_F = 20\text{ mA}$, $t_p = 20\text{ ms}$)	(typ (max))	V_F	1.3 (≤ 1.6)	V
Reverse current	(typ (max))	I_R	not designed for reverse operation	μA
Total radiant flux ($I_F = 20\text{ mA}$, $t_p = 20\text{ ms}$)	(typ)	Φ_e	10	mW

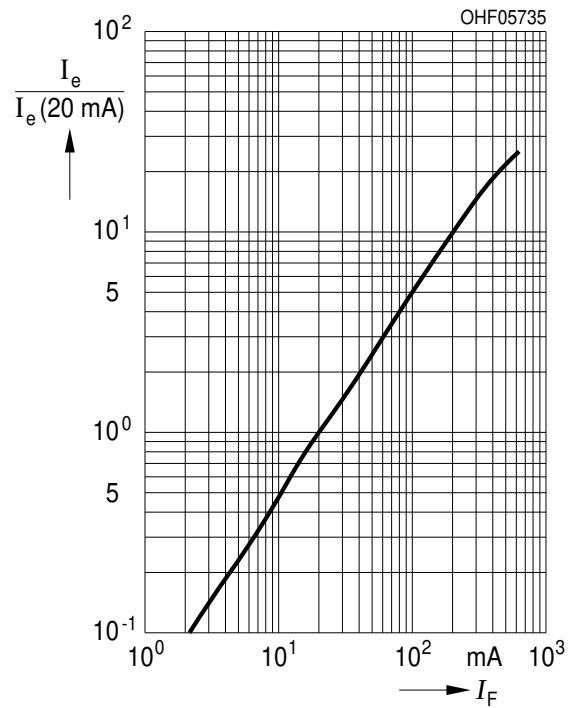
Parameter		Symbol	Values	Unit
Radiant intensity ($I_F = 20 \text{ mA}$, $t_p = 20 \text{ ms}$)	(typ)	$I_{e, \text{typ}}$	3	mW/sr
Radiant intensity ($I_F = 20 \text{ mA}$, $t_p = 20 \text{ ms}$)	(min)	$I_{e, \text{min}}$	1.5	mW/sr
Temperature coefficient of I_e or Φ_e ($I_F = 20 \text{ mA}$, $t_p = 20 \text{ ms}$)	(typ)	TC_I	-0.3	% / K
Temperature coefficient of V_F ($I_F = 20 \text{ mA}$, $t_p = 20 \text{ ms}$)	(typ)	TC_V	-0.8	mV / K
Temperature coefficient of wavelength ($I_F = 20 \text{ mA}$, $t_p = 20 \text{ ms}$)	(typ)	TC_λ	0.3	nm / K

Diagrams**Emitter 1****Relative Spectral Emission** ^{2) page 19}

$$I_{\text{rel}} = f(\lambda), T_A = 25^\circ\text{C}$$

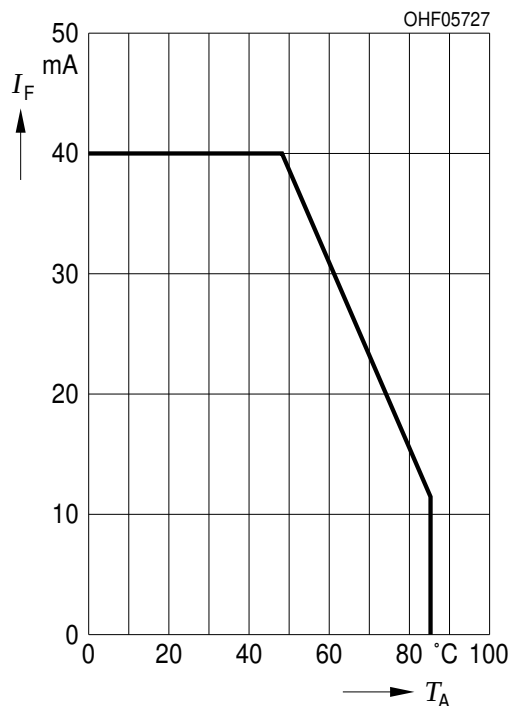
**Radiant Intensity** ^{2) page 19}

$$I_e / I_e(20 \text{ mA}) = f(I_F), \text{ single pulse, } t_p = 25 \mu\text{s}, T_A = 25^\circ\text{C}$$

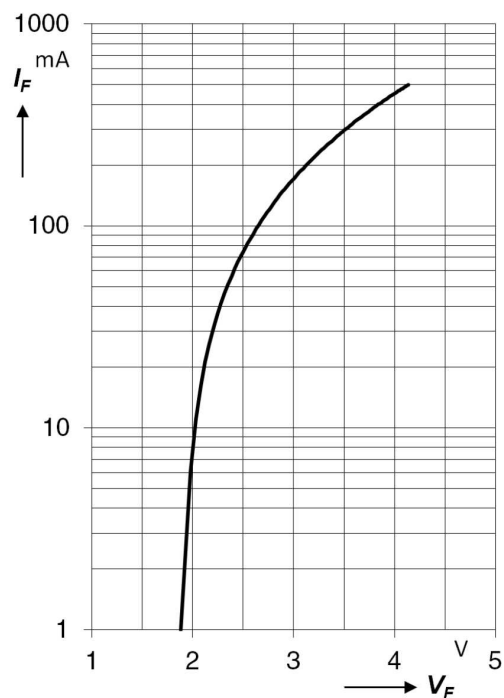


Max. Permissible Forward Current

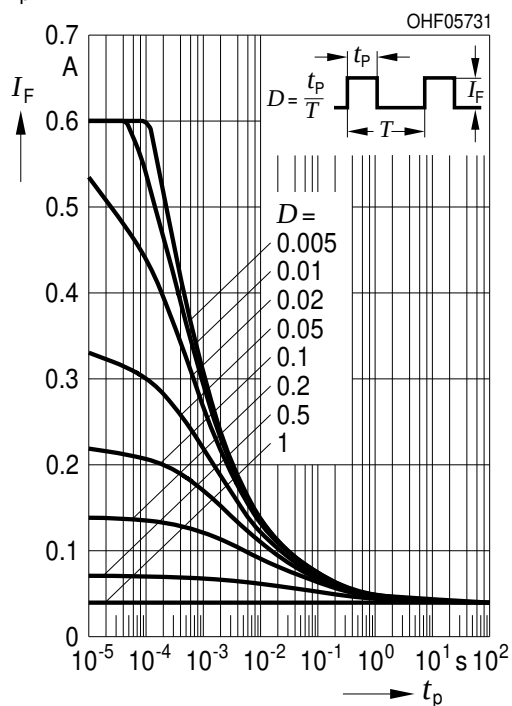
$$I_{F, \max} = f(T_A), R_{thJA} = 445 \text{ K / W}$$

**Forward Current** ^{2) page 19}

$$I_F = f(V_F), \text{ single pulse, } t_p = 100 \mu\text{s}, T_A = 25^\circ\text{C}$$

**Permissible Pulse Handling Capability**

$$I_F = f(t_p), T_A = 25^\circ\text{C}, \text{ duty cycle } D = \text{parameter}$$

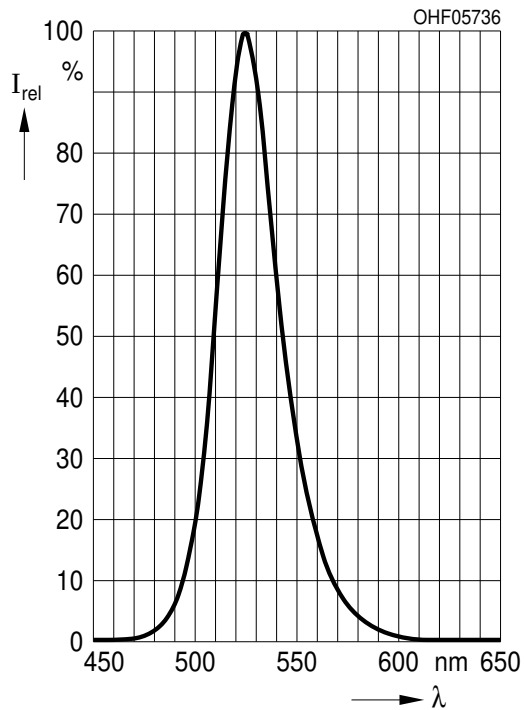


Diagrams

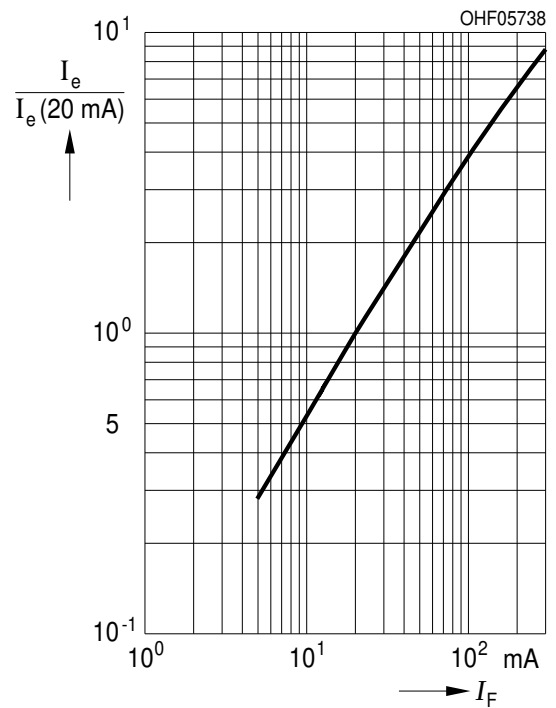
Emitter 2

Relative Spectral Emission ^{2) page 19}

$$I_{\text{rel}} = f(\lambda), T_A = 25^\circ\text{C}$$

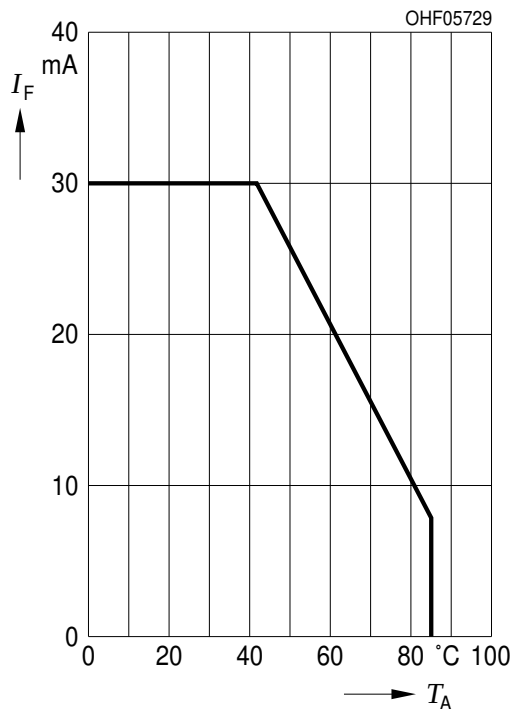
Radiant Intensity ^{2) page 19}

$$I_e / I_e(20 \text{ mA}) = f(I_F), \text{ single pulse, } t_p = 25 \mu\text{s}, T_A = 25^\circ\text{C}$$

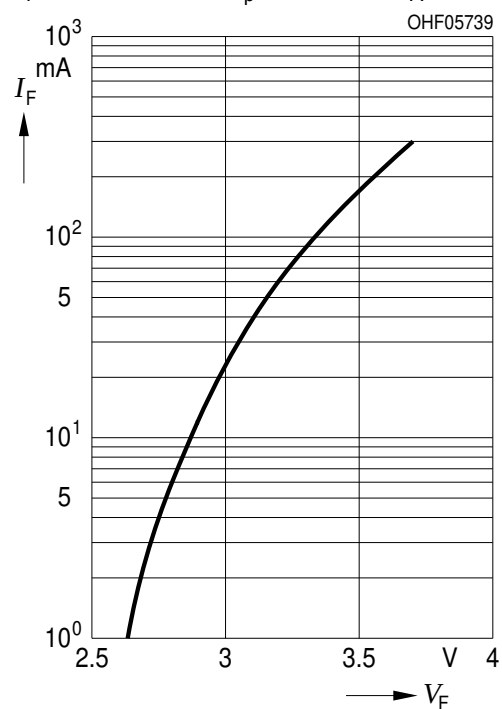


Max. Permissible Forward Current

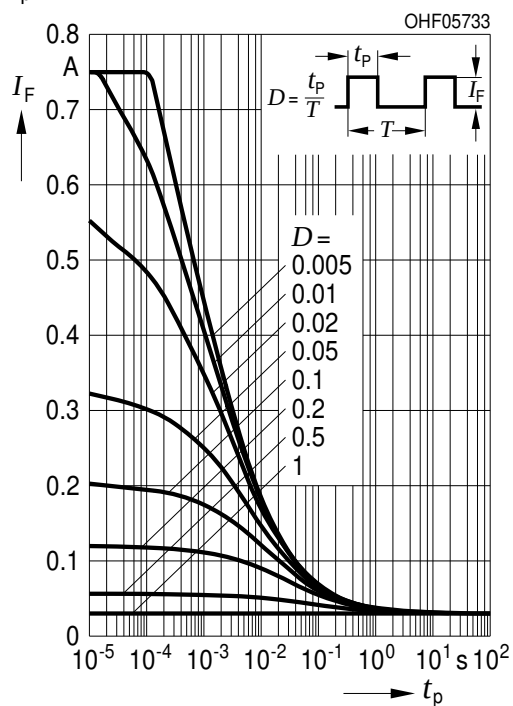
$$I_{F, \max} = f(T_A), R_{thJA} = 565 \text{ K / W}$$

**Forward Current** ^{2) page 19}

$$I_F = f(V_F), \text{ single pulse, } t_p = 100 \mu\text{s}, T_A = 25^\circ\text{C}$$

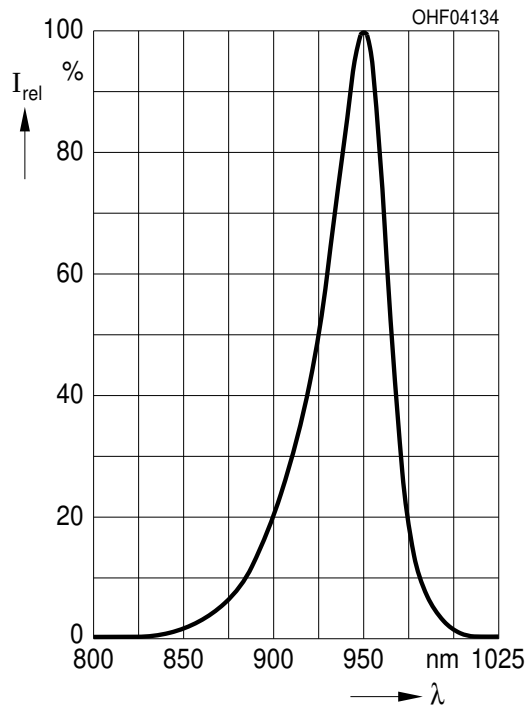
**Permissible Pulse Handling Capability**

$$I_F = f(t_p), T_A = 25^\circ\text{C}, \text{ duty cycle } D = \text{parameter}$$

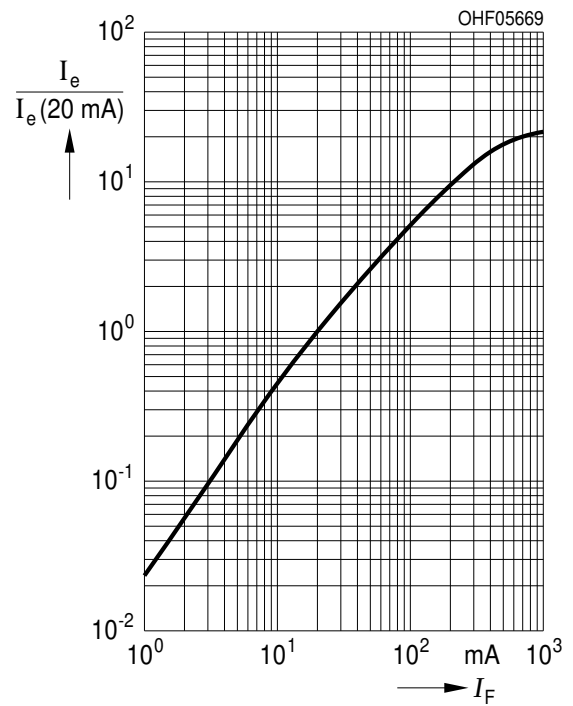


Diagrams**Emitter 3****Relative Spectral Emission** ^{2) page 19}

$$I_{\text{rel}} = f(\lambda), T_A = 25^\circ\text{C}$$

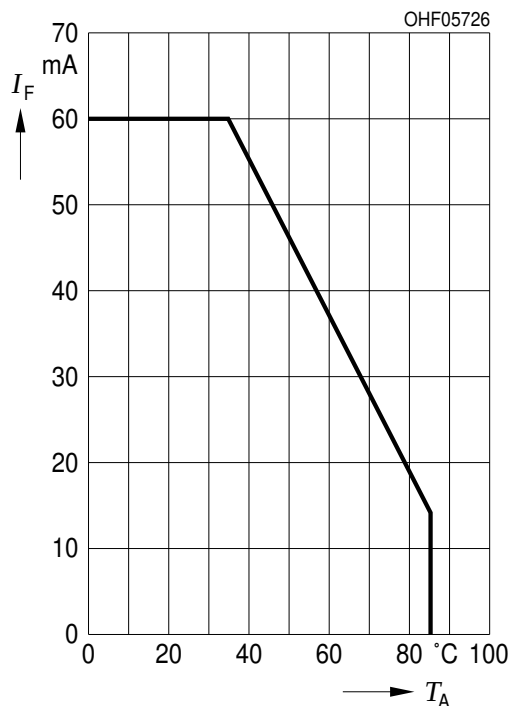
**Radiant Intensity** ^{2) page 19}

$$I_e / I_e(20 \text{ mA}) = f(I_F), \text{ single pulse, } t_p = 100 \mu\text{s}, T_A = 25^\circ\text{C}$$

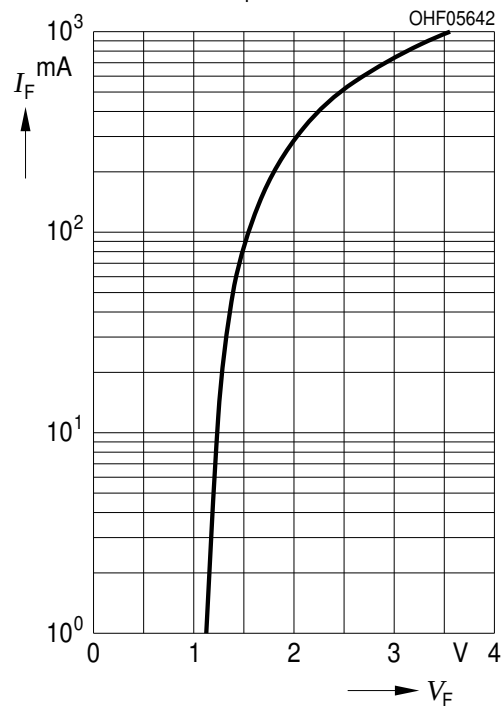


Max. Permissible Forward Current

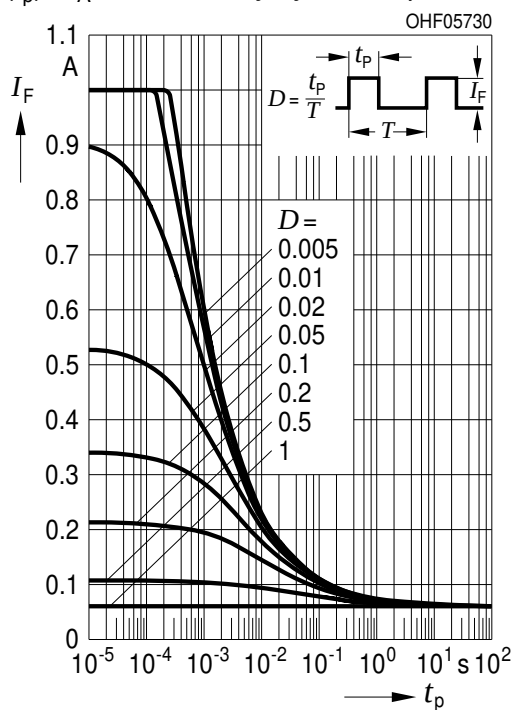
$$I_{F, \max} = f(T_A), R_{thJA} = 585 \text{ K / W}$$

**Forward Current** ^{2) page 19}

$$I_F = f(V_F), \text{ single pulse, } t_p = 100 \mu\text{s}, T_A = 25^\circ\text{C}$$

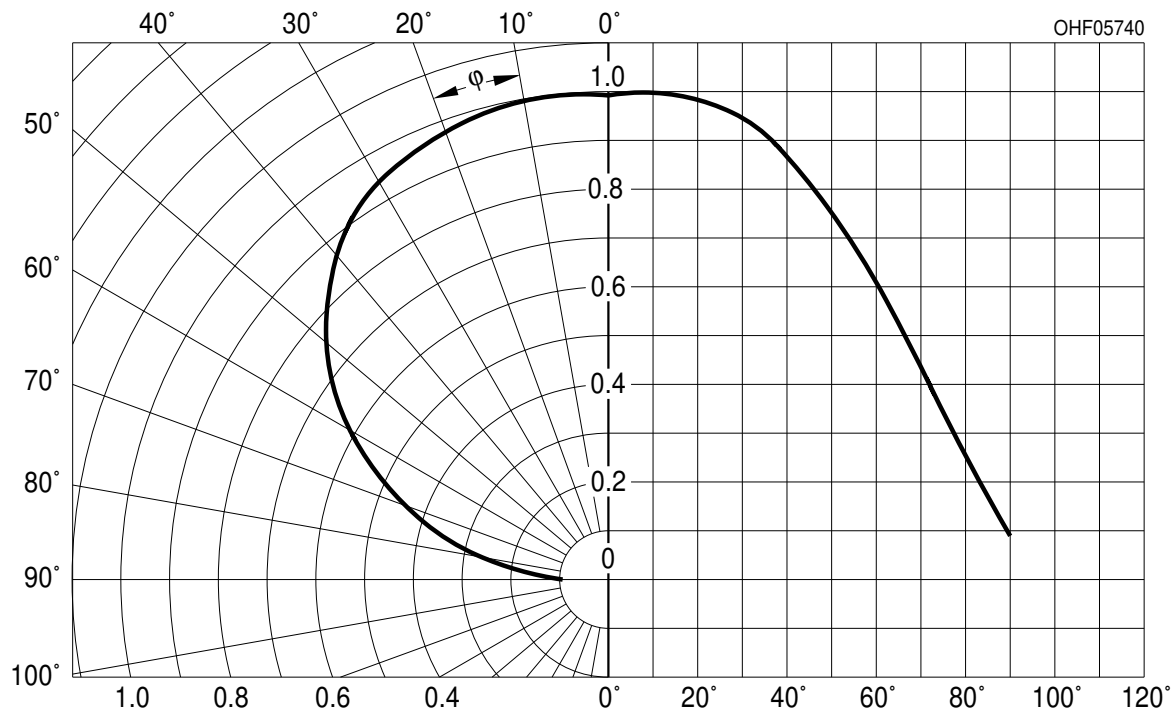
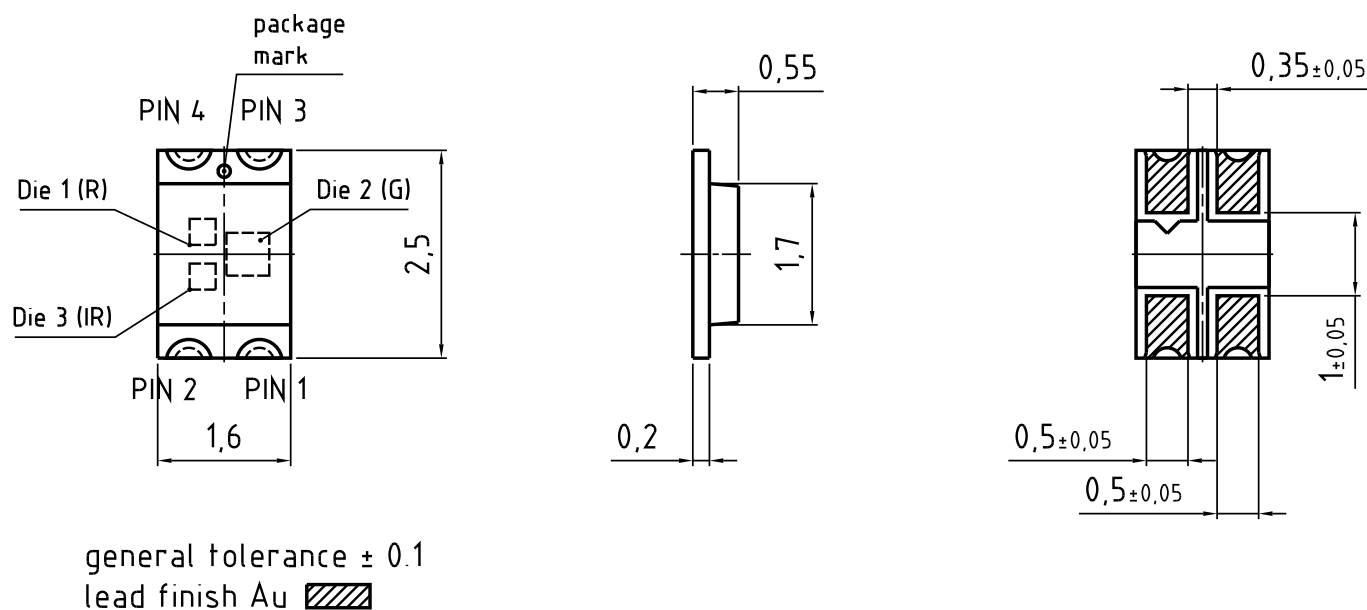
**Permissible Pulse Handling Capability**

$$I_F = f(t_p), T_A = 25^\circ\text{C}, \text{ duty cycle } D = \text{parameter}$$



Radiation Characteristics ^{2) page 19}

$$I_{\text{rel}} = f(\phi), T_A = 25^\circ\text{C}$$

**Package Outline**

Dimensions in mm.

C63062-A4322-A2-01

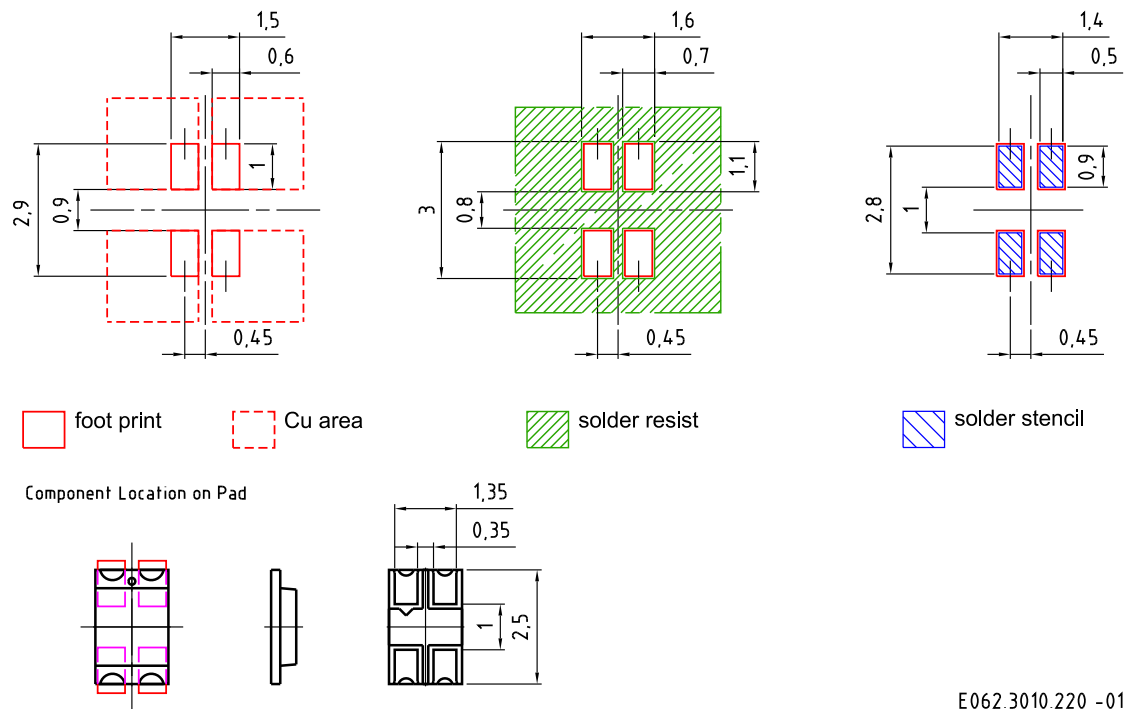
Pinning

Pin	Description
1	Cathode Emitter 2 (530 nm)
2	Cathode Emitter 3 (940 nm)
3	Anode Emitter 1/2/3
4	Cathode Emitter 1 (655 nm)

Approximate Weight:

6 mg

Recommended Solder Pad

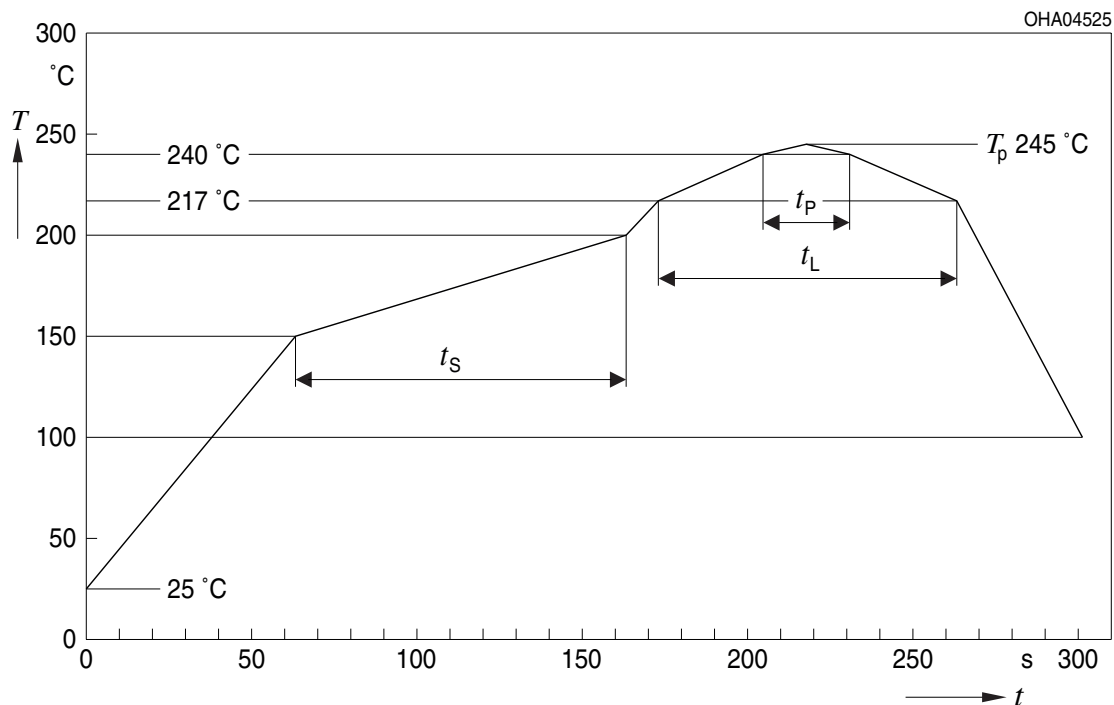


Dimensions in mm.

E062.3010.220 -01

Reflow Soldering Profile

Product complies to MSL Level 3 acc. to JEDEC J-STD-020E

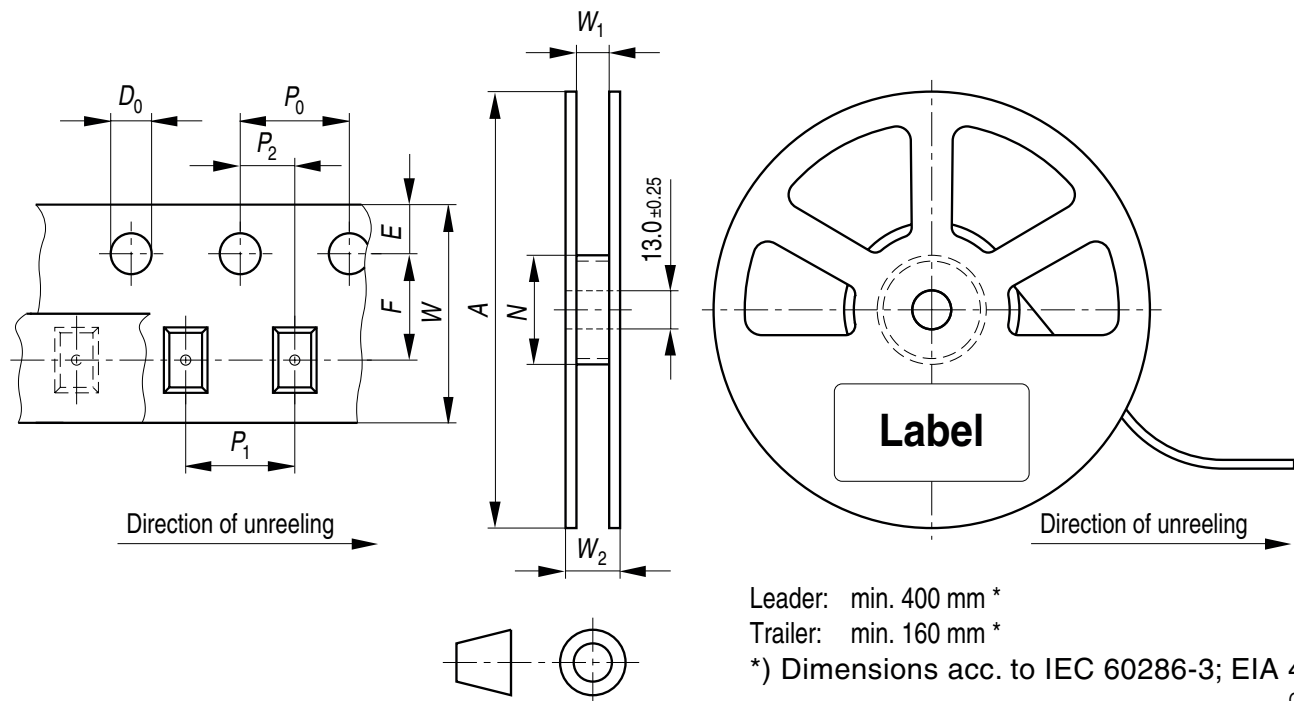
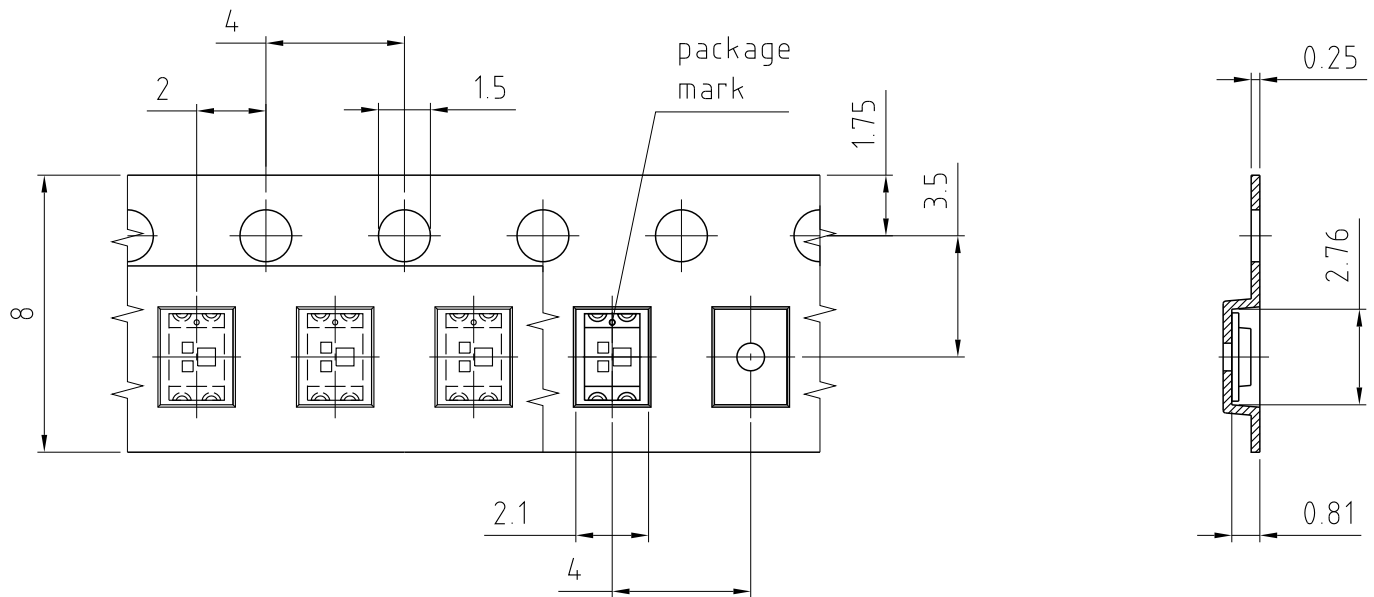


OHA04612

Profile Feature Profil-Charakteristik	Symbol Symbol	Pb-Free (SnAgCu) Assembly			Unit Einheit
		Minimum	Recommendation	Maximum	
Ramp-up rate to preheat*) 25°C to 150°C			2	3	K/s
Time t_S T_{Smin} to T_{Smax}	t_S	60	100	120	s
Ramp-up rate to peak*) T_{Smax} to T_P			2	3	K/s
Liquidus temperature	T_L	217			$^{\circ}\text{C}$
Time above liquidus temperature	t_L		80	100	s
Peak temperature	T_P		245	260	$^{\circ}\text{C}$
Time within 5°C of the specified peak temperature $T_P - 5\text{ K}$	t_P	10	20	30	s
Ramp-down rate* T_P to 100°C			3	6	K/s
Time 25°C to T_P				480	s

All temperatures refer to the center of the package, measured on the top of the component

* slope calculation DT/Dt : Dt max. 5 s; fulfillment for the whole T-range



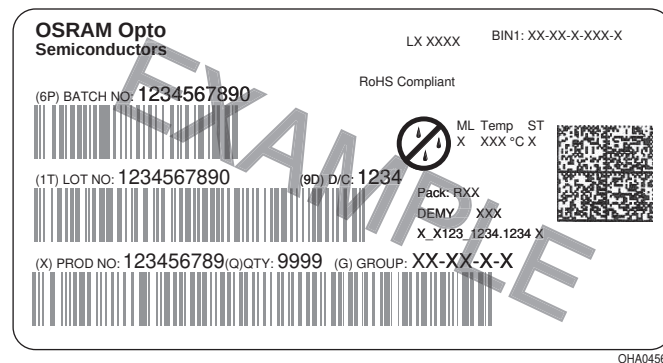
Tape dimensions [mm]

W	P ₀	P ₁	P ₂	D ₀	E	F
8 + 0.3 / -0.1	4 ± 0.1	2 ± 0.05 or 4 ± 0.1	2 ± 0.05	1.5 ± 0.1	1.75 ± 0.1	3.5 ± 0.05

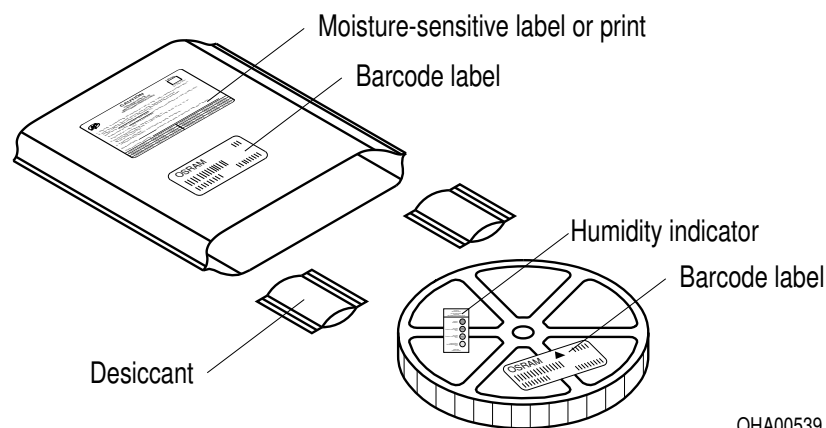
Reel dimensions [mm]

A	W	N _{min}	W ₁	W _{2max}
180	8	60	8.4 + 2	14.4

Barcode-Product-Label (BPL)



Dry Packing Process and Materials

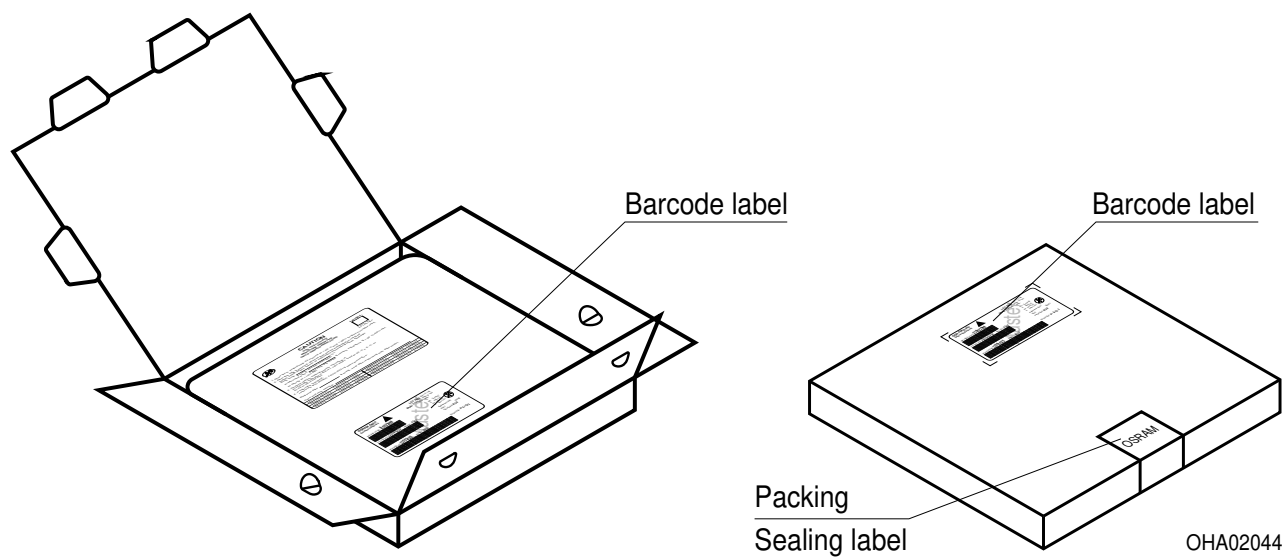


Note:

Moisture-sensitive product is packed in a dry bag containing desiccant and a humidity card.

Regarding dry pack you will find further information in the internet. Here you will also find the normative references like JEDEC.

Transportation Packing and Materials



Dimensions of transportation box in mm

Width	Length	Height
200 ± 5	195 ± 5	30 ± 5

Disclaimer

Language english will prevail in case of any discrepancies or deviations between the two language wordings.

Attention please!

The information describes the type of component and shall not be considered as assured characteristics.

Terms of delivery and rights to change design reserved. Due to technical requirements components may contain dangerous substances.

For information on the types in question please contact our Sales Organization.

If printed or downloaded, please find the latest version in the Internet.

Packing

Please use the recycling operators known to you. We can also help you – get in touch with your nearest sales office.

By agreement we will take packing material back, if it is sorted. You must bear the costs of transport. For packing material that is returned to us unsorted or which we are not obliged to accept, we shall have to invoice you for any costs incurred.

Components used in life-support devices or systems must be expressly authorized for such purpose!

Critical components* may only be used in life-support devices** or systems with the express written approval of OSRAM OS.

*) A critical component is a component used in a life-support device or system whose failure can reasonably be expected to cause the failure of that life-support device or system, or to affect its safety or the effectiveness of that device or system.

**) Life support devices or systems are intended (a) to be implanted in the human body, or (b) to support and/or maintain and sustain human life. If they fail, it is reasonable to assume that the health and the life of the user may be endangered.

Glossary

¹⁾ only one chip on

²⁾ **Typical Values:** Due to the special conditions of the manufacturing processes of LED, the typical data or calculated correlations of technical parameters can only reflect statistical figures. These do not necessarily correspond to the actual parameters of each single product, which could differ from the typical data and calculated correlations or the typical characteristic line. If requested, e.g. because of technical improvements, these typ. data will be changed without any further notice.

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